

Form 1349 (Modified)

Information Disclosure
Statement By Applicant

(Use Several Sheets if Necessary)

Atty Docket No.

MAT-4

Applicants:

Rene George et al

Filing Date

9/17/03

Serial No.:

10/665,267

Group

1763 2813

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
HD	A	US 6,524,936 B2	2/25/03	Hallock et al			
HD	B	US 6,342,446 B1	1/29/2003	Smith et al			
HD	C	US 6,426,304 B1	6/30/2002	Chien et al			
HD	D	US 6,379,576 B2	4/30/2002	Luo et al			
HD	E	US 6,352,936 B1	3/5/2002	Jehoul et al			
HD	F	US 6,342,446 B1	1/29/2002	Smith et al			
HD	G	US 6,277,733 B1	8/21/2001	Smith			
HD	H	US 6,251,771 B1	6/26/2001	Smith et al			
HD	I	5,628,871	5/13/1997	Shinagawa			
HD	J	5,534,231	7/9/1996	Savas			
HD	K	5,403,436	4/4/1995	Fujimura et al			
HD	L	4,980,022	12/25/1990	Fujimura et al			
HD	M	4,861,732	8/29/1989	Fujimura et al			
HD	N	4,861,424	8/29/1989	Fujimura et al			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation	
							Yes	No
HD	0							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
HD	P	Boumerzoug et al, A Dry Process For Polymer Sidewall Residue Removal After Via-Hole Etching, 11/12/2000, 11 th Annual IEEE/SEMI Advanced Semiconductor Manufacturing Conference and Workshop, Boston, MA (ASMC 2000)
HD	Q	Xu et al, Dry Cleaning Technologies For Post Metal And Via Applications, 7/13/1998, Symposium on Contamination Free Manufacturing for Semiconductor Processing, Semicon West 98, San Francisco, CA.
HD	R	Hu et al, Resist Stripping for Multilevel Interconnect Integrating Low k Dielectric Material, 2/2000, AVS First International Conference on Microelectronics and Interfaces.
HD	S	Gooch et al, Elimination Solvents From Semiconductor Wafer Manufacturing, 7/1/1999, 3 rd Green Chemistry and Engineering Conference, Washington DC.
HD	T	Dopp et al, Manufacturing Qualifications of an All-Dry Via Deveil Plasma Process, 5/2000, 197 th Electrochemical Society Meeting, Toronto, Canada.
Examiner		Date Considered
Nathan Orry		10/21/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)

Information Disclosure
Statement By Applicant

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MAT-4

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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
HD	A	US2002/0110992 A1	8/15/2002	Ho			

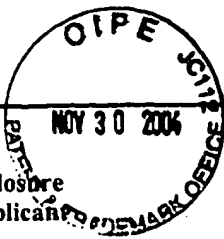
Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
Examiner		Date Considered
	Heath, R. D. et al	10/20/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified)

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U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date
HD	A	US2002/0110992 A1	8/15/2002	Ho			
HD	B	5,770,100	6/23/1998	Fukuyama			
HD	C	US 6,265,320 B1	7/24/2001	Shi et al			

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub- class	Translation	
							Yes	No

Other Documents

Examiner	No.	Author, Title, Date, Place (e.g. Journal) of Publication
Examiner		Date Considered
Heather A. Doty		10/20/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.